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Simulation of Single Event Upset in SRAMs Induced by low Energy Proton With Geant4

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The architecture of SRAM and single event upset cross section computation approach are presented. Deposited energy and single event upset cross section are analyzed by the simulation of single event upset in different characteristic dimensions SRAMs induced by low energy proton using Monte-Carlo code Geant4. The simulating result shows that the deposited energy will decrease with the increase of incident proton energy, but it will increase with the increase of characteristic dimensions in the 1-5MeV energy range. And the SEU cross section will decrease with the increase of incident proton energy, but it will increase with the decrease of critical charge in the 1-5MeV energy range.

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